

Appl. No.: 10/051,623
Amdt. Dated: 02/05/2004
Off. Act. Dated: 09/05/2003

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claims 1-48 (canceled)

49. (currently amended): A layer of material for use in connection with microcircuits, said layer being expunged from a solid base material, wherein said layer has a surface with a non-planar contour defined by the relative positions of a plurality of acceptor centers in a solid base material from which said layer is formed, and wherein said layer is thereby adapted for use in connection with microcircuits.

50. (previously presented): A layer of material as recited in claim 49, wherein said layer is formed by the steps comprising:

- (a) introducing a plurality of acceptor centers into said base material;
- (b) introducing a plurality of atoms into said base material at a location spaced apart from the location of said acceptor centers;
- (c) transporting said atoms toward said acceptor centers; and
- (d) expunging said layer from said base material in the region of said acceptor centers, whereby said expunged layer has said surface with a contour defined by said relative positions of said acceptor centers.

51. (previously presented): A layer of material as recited in claim 49, wherein said base material comprises a semiconductor material.

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52. (previously presented): A layer of material as recited in claim 51, wherein said semiconductor material comprises silicon.

53. (previously presented): A layer of material as recited in claim 50, wherein said atoms comprise hydrogen atoms.

54. (previously presented): A layer of material as recited in claim 49, wherein said acceptor centers are formed by introducing a getter material into said base material.

55. (previously presented): A layer of material as recited in claim 54, wherein said base material comprises silicon and said getter material is selected from the group consisting of Group III materials.

56. (previously presented): A layer of material as recited in claim 54, wherein said base material comprises silicon and said getter material is selected from the group consisting of gallium and boron.

57. (currently amended): A layer of material for use in connection with microcircuits, said layer being expunged from a solid base material, wherein said layer has a surface with a non-planar contour defined by the relative positions of a plurality of acceptor centers in a solid base material from which said layer is formed, wherein said layer is thereby adapted for use in connection with microcircuits, and wherein said layer is formed by the steps comprising:

- (a) introducing a plurality of acceptor centers into said base material;
- (b) introducing a plurality of atoms into said base material at a location spaced apart from the location of said acceptor centers;
- (c) transporting said atoms toward said acceptor centers; and

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(d) expunging said layer from said base material in the region of said acceptor centers, whereby said expunged layer has said surface with a contour defined by said relative positions of said acceptor centers.

58. (previously presented): A layer of material as recited in claim 57, wherein said base material comprises a semiconductor material.

59. (previously presented): A layer of material as recited in claim 58, wherein said semiconductor material comprises silicon.

60. (previously presented): A layer of material as recited in claim 57, wherein said atoms comprise hydrogen atoms.

61. (previously presented): A layer of material as recited in claim 57, wherein said acceptor centers are formed by introducing a getter material into said base material.

62. (previously presented): A layer of material as recited in claim 61, wherein said base material comprises silicon and said getter material is selected from the group consisting of Group III materials.

63. (previously presented): A layer of material as recited in claim 61, wherein said base material comprises silicon and said getter material is selected from the group consisting of gallium and boron.

64. (currently amended): A layer of material for use in connection with microcircuits, said layer being expunged from a solid base material, wherein said layer has a surface with a non-planar contour defined by the relative positions of a plurality of

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acceptor centers in a solid semiconductor material from which said layer is formed, wherein said layer is thereby adapted for use in connection with microcircuits, and wherein said layer is formed by the steps comprising:

- (a) introducing a plurality of acceptor centers into said semiconductor material;
- (b) introducing a plurality of atoms into said semiconductor material at a location spaced apart from the location of said acceptor centers;
- (c) transporting said atoms toward said acceptor centers; and
- (d) expunging said layer from said base material in the region of said acceptor centers, whereby said expunged layer has said surface with a contour defined by said acceptor centers.

65. (previously presented): A layer of material as recited in claim 64, wherein said semiconductor material comprises silicon.

66. (previously presented): A layer of material as recited in claim 64, wherein said atoms comprise hydrogen atoms.

67. (previously presented): A layer of material as recited in claim 64, wherein said acceptor centers are formed by introducing a getter material into said semiconductor material.

68. (previously presented): A layer of material as recited in claim 67, wherein said semiconductor material comprises silicon and said getter material is selected from the group consisting of Group III materials.

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69. (previously presented): A layer of material as recited in claim 67, wherein said semiconductor material comprises silicon and said getter material is selected from the group consisting of gallium and boron.

70. (currently amended): A layer of material for use in connection with microcircuits, said layer being expunged from a solid base material, wherein said layer has a surface with a non-planar contour defined by the relative positions of a plurality of acceptor centers in a solid silicon material from which said layer is formed, wherein said layer is thereby adapted for use in connection with microcircuits, and wherein said layer is formed by the steps comprising:

- (a) introducing a plurality of acceptor centers into said silicon material;
- (b) introducing a plurality of atoms into said silicon material at a location spaced apart from the location of said acceptor centers;
- (c) transporting said atoms toward said acceptor centers; and
- (d) expunging said layer from said base material in the region of said acceptor centers, whereby said expunged layer has said surface with a contour defined by said acceptor centers.

71. (previously presented): A layer of material as recited in claim 70, wherein said atoms comprise hydrogen atoms.

72. (previously presented): A layer of material as recited in claim 70, wherein said acceptor centers are formed by introducing a getter material into said silicon material.

73. (previously presented): A layer of material as recited in claim 72, wherein said getter material is selected from the group consisting of Group III materials.

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74. (previously presented): A layer of material as recited in claim 72, wherein said getter material is selected from the group consisting of gallium and boron.

75. (currently amended): A base material for use in connection with fabrication of microcircuits, wherein said base material includes a non-planar contour line along which a layer can be expunged, said contour line defined by the relative positions of a plurality of acceptor centers in said base material.

76. (previously presented): A material as recited in claim 75, wherein said base material is processed according to the steps comprising:

- (a) introducing a plurality of acceptor centers into said base material;
- (b) introducing a plurality of atoms into said material at a location spaced apart from the location of said acceptor centers; and
- (c) transporting said atoms toward said acceptor centers.

77. (previously presented): A layer of material as recited in claim 75, wherein said base material comprises a semiconductor material.

78. (previously presented): A layer of material as recited in claim 77, wherein said semiconductor material comprises silicon.

79. (previously presented): A layer of material as recited in claim 76, wherein said atoms comprise hydrogen atoms.

80. (previously presented): A layer of material as recited in claim 75, wherein said acceptor centers are formed by introducing a getter material into said base material.

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81. (previously presented): A layer of material as recited in claim 80, wherein said base material comprises silicon and said getter material is selected from the group consisting of Group III materials.

82. (previously presented): A layer of material as recited in claim 80, wherein said base material comprises silicon and said getter material is selected from the group consisting of gallium and boron.